

## **Dual P-Channel MOSFET**

-60V, -12A,  $68m\Omega$ 

#### **FEATURES**

- Fast switching
- Low thermal resistance package
- Low profile package
- Pb-free plating
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

			TI	$\sim$	
 		. 4			~

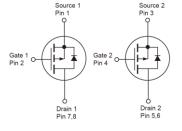
- Power Supply
- Motor Control

KEY PERFORMANCE PARAMETERS					
PARA	METER	VALUE	UNIT		
V <sub>DS</sub>		-60	V		
R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V	68	0		
(max)	(max) $V_{GS} = -4.5V$		mΩ		
	${\sf Q}_{\sf g}$	16.4	nC		









**Dual P-Channel MOSFET** 

Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	$V_{DS}$	-60	V		
Gate-Source Voltage	$V_{GS}$	±20	V		
Continuous Drain Current (Note 1)	T <sub>C</sub> = 25°C	I <sub>D</sub>	-12	Δ	
Continuous Drain Current	T <sub>C</sub> = 100°C		-8	A	
Pulsed Drain Current (Note 2)	I <sub>DM</sub>	-48	А		
Total Power Dissipation @ T <sub>C</sub> = 25°C	$P_{DTOT}$	3.5	W		
Single Pulsed Avalanche Energy (Note 3)	E <sub>AS</sub>	7.2	mJ		
Single Pulsed Avalanche Current (Note 3)	I <sub>AS</sub>	12	А		
Operating Junction and Storage Tempera	$T_J,T_STG$	- 55 to +150	°C		

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Case Thermal Resistance	R <sub>eJC</sub>	4.5	°C/W		
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	85	°C/W		

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)					1	1
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV <sub>DSS</sub>	-60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1.2	-1.6	-2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
	$V_{DS} = -60V, V_{GS} = 0V$	I <sub>DSS</sub>			-1	μА
Zero Gate Voltage Drain Current	V <sub>DS</sub> = -48V, Tc = 125°C				-10	
	$V_{GS} = -10V, I_D = -6A$			54	68	mΩ
Drain-Source On-State Resistance	$V_{GS} = -4.5V, I_{D} = -3A$	R <sub>DS(on)</sub>		90	110	
Forward Transconductance	$V_{DS} = -10V, I_{D} = -6A$	g <sub>fs</sub>		8.5		S
Dynamic (Note 5)						
Total Gate Charge		$Q_g$		16.4		nC
Gate-Source Charge	$V_{DS} = -30V, I_{D} = -6A,$ $V_{GS} = -10V$	$Q_{gs}$		2.8		
Gate-Drain Charge		$Q_{gd}$		3.6		
Input Capacitance		C <sub>iss</sub>		870		
Output Capacitance	$V_{DS} = -30V, V_{GS} = 0V,$	C <sub>oss</sub>		70		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		42		
Switching (Note 6)					1	1
Turn-On Delay Time		t <sub>d(on)</sub>		8.3		
Turn-On Rise Time	$V_{DD} = -30V, I_{D} = -1A,$	t <sub>r</sub>		42.4		
Turn-Off Delay Time	$R_{GEN}=6\Omega$	t <sub>d(off)</sub>		64.6		ns
Turn-Off Fall Time		t <sub>f</sub>		16.4		
Source-Drain Diode (Note 4)						
Maximum Continuous Drain-Source		1			-12	A
Diode Forward Current	Integral reverse diode	I <sub>S</sub>			-12	_ ^
Maximum Pulse Drain-Source	in the MOSFET	I <sub>SM</sub>			-48	Α
Diode Forward Current	2/ 2/ 44	-				
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = -1A$	$V_{SD}$			-1	V

#### Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 0.1 mH,  $I_{AS} = -12 A$ ,  $V_{DD} = -25 V$ ,  $R_G = 25 \Omega$ , Starting  $T_J = 25 ^{\circ} C$
- 4. Pulse test: PW  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.

Version: B1710



Taiwan Semiconductor

# **ORDERING INFORMATION (EXAMPLE)**

PART NO.	PACKAGE	PACKING
TSM680P06DPQ56 RLG	PDFN56 Dual	2,500pcs / 13"Reel

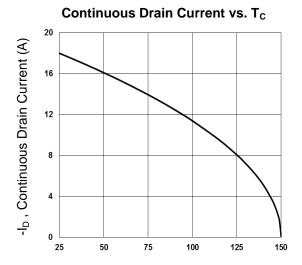
#### Note:

- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition

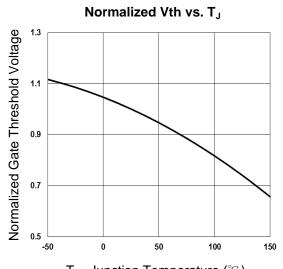


#### CHARACTERISTICS CURVES

(T<sub>C</sub> = 25°C unless otherwise noted)

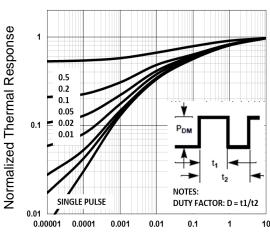


T<sub>C</sub> , Case Temperature (°C)

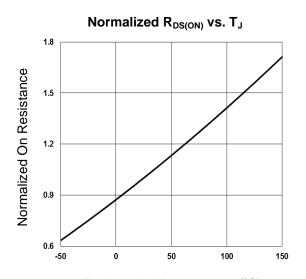


 $\mathsf{T}_\mathsf{J}$  , Junction Temperature (°C)

**Normalized Transient Impedance** 

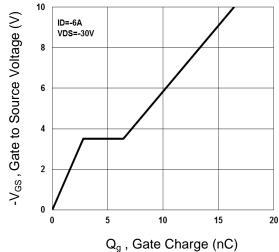


Square Wave Pulse Duration

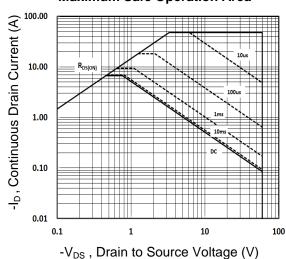


T<sub>J</sub>, Junction Temperature (°C)





**Maximum Safe Operation Area** 



0.51 ±0.10

3.58 ±0.20

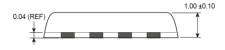
1.10 (Min)

0.61 ±0.10

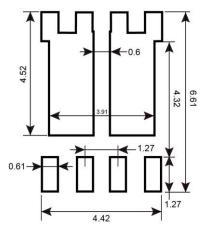


## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

# 



## SUGGESTED PAD LAYOUT (Unit: Millimeters)



## **MARKING DIAGRAM**



Y = Year Code

**M** = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code (1~9, A~Z)

Version: B1710



Taiwan Semiconductor

### **Notice**

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.